

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	550	(light adj emitting adj diode) and gan and substrate and (si silicon)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/01/21 12:21
2	BRS	L2	548	1 and @ay<2002	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/01/21 12:01
3	BRS	L3	54	(light adj emitting adj diode) and gan and ((si silicon) adj substrate) and (cover window)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/01/21 12:50
4	BRS	L4	98	(cover adj glass) and (light adj emitting adj diode) and substrate	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/01/21 13:16
5	BRS	L5	1233	257/98.ccls. and @ay<2002	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/01/21 13:58
6	BRS	L6	1757	362/\$.ccls. and @ay<2002 and (light adj emitting adj diode)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2003/01/21 14:01